

## EECS 42 Introduction Digital Electronics Andrew R. Neureuther

2<sup>nd</sup> Midterm 11/6 See Coverage Sheet

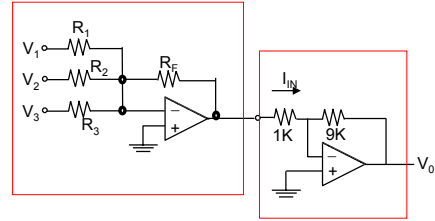
### Lecture # 19 Logic Transients

Handout of Wed Lecture.

- A) Quiz
- B) Worst Case CMOS Delay
- C) Delay in CMOS Cascade

<http://inst.EECS.Berkeley.EDU/~ee42/>

### CASCADE OP-AMP CIRCUITS



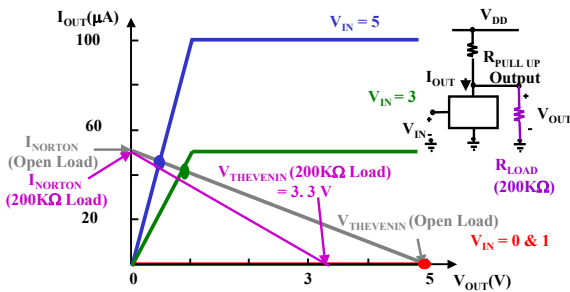
How do you get started on finding  $V_O$ ?

Hint: Identify Stages

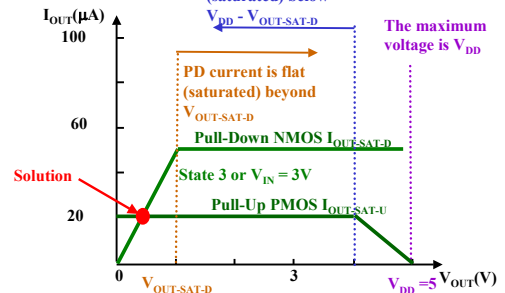
Hint:  $I_{IN}$  does not affect  $V_{O1}$

See the further examples of op-amp circuits in the reader

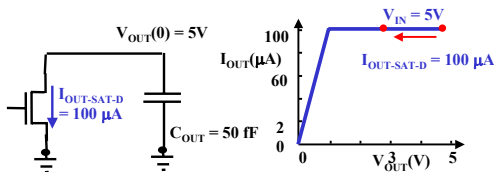
### Composite Current Plot for the 42S\_NMOS Circuit with 200k $\Omega$ Load to Ground



### Composite $I_{OUT}$ vs. $V_{OUT}$ for CMOS



### Output Propagation Delay High to Low (Cont.)



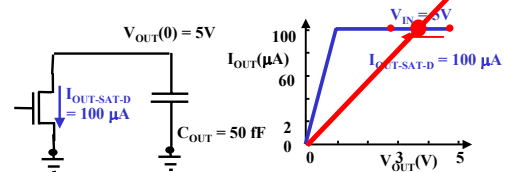
When  $V_{OUT} > V_{OUT-SAT-D}$  the available current is  $I_{OUT-SAT-D}$

For this circuit when  $V_{OUT} > V_{OUT-SAT-D}$  the available current is constant at  $I_{OUT-SAT-D}$  and the capacitor discharges.

The propagation delay is thus

$$\Delta t = \frac{C_{OUT} \Delta V}{I_{OUT-SAT-D}} = \frac{C_{OUT} V_{DD}}{2 I_{OUT-SAT-D}} = \frac{50 \text{ fF} \cdot 2.5 \text{ V}}{100 \mu\text{A}} = 1.25 \text{ ns}$$

### $R_D = \frac{3}{4} V_{DD} / I_{SAT}$ has a Physical Interpretation



$\frac{3}{4} V_{DD}$  is the average value of  $V_{OUT}$

Approximate the NMOS device curve by a straight line from (0,0) to  $(I_{OUT-SAT-D}, \frac{3}{4} V_{DD})$ .

Interpret the straight line as a resistor with slope =  $1/R = \frac{3}{4} V_{DD} / I_{SAT}$

### Switched Equivalent Resistance Values

The resistor values depend on the properties of silicon, geometrical layout, design style and technology node.

n-type silicon has a carrier mobility that is 2 to 3 times higher than p-type.

The resistance is inversely proportion to the gate width/length in the geometrical layout.

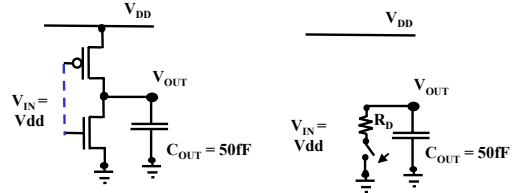
Design styles may restrict all NMOS and PMOS to be of a predetermined fixed size.

The current per unit width of the gate increases nearly inversely with the linewidth.

**For convenience in EE 42 we assume**  
 $R_p = R_u = 10 \text{ k}\Omega$  for  $V_{DD} = 5V$  and  
 $R_n = R_l = 10 \text{ k}\Omega$  for  $V_{DD} = 5V$

### Inverter Propagation Delay

Discharge (pull-down)



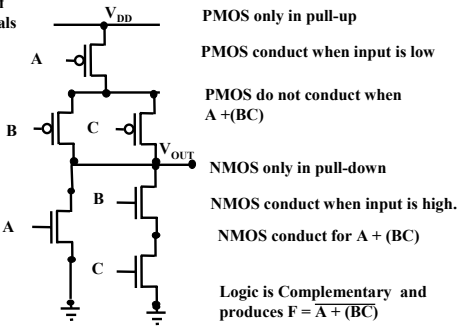
$$\Delta t = 0.69R_D C_{OUT} = 0.69(10\text{k}\Omega)(50\text{fF}) = 345 \text{ ps}$$

Discharge (pull-up)

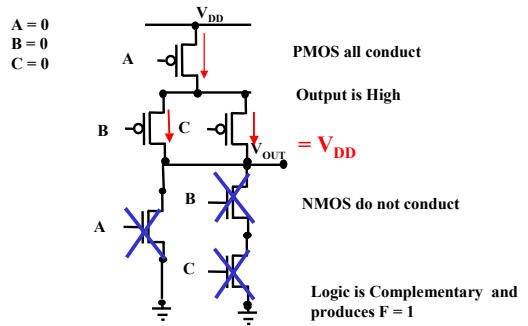
$$\Delta t = 0.69R_U C_{OUT} = 0.69(10\text{k}\Omega)(50\text{fF}) = 345 \text{ ps}$$

NMOS and PMOS use the same set of input signals

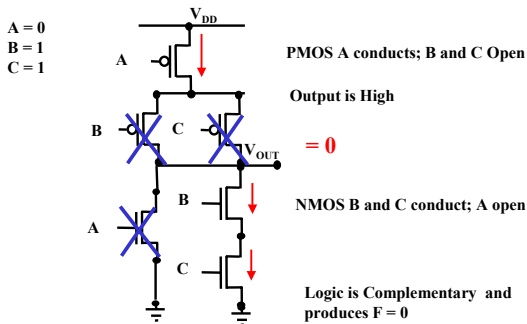
### CMOS Logic Gate



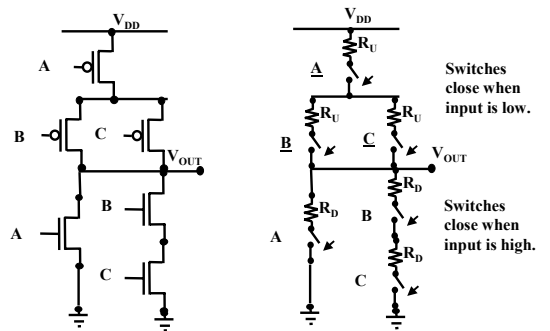
### CMOS Logic Gate: Example Inputs



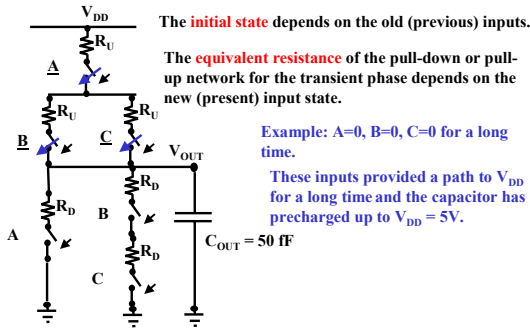
### CMOS Logic Gate: Example Inputs



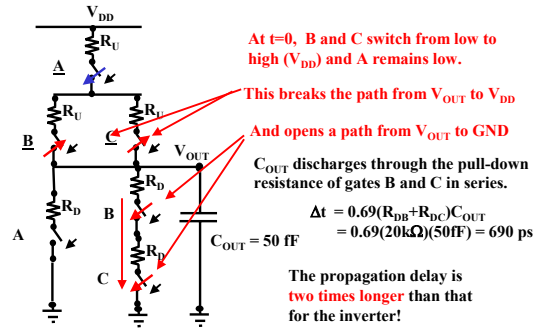
### Switched Equivalent Resistance Network



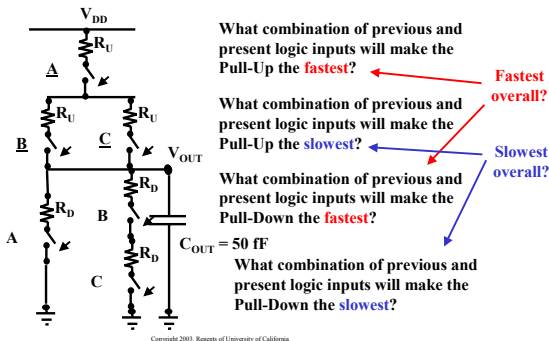
### Logic Gate Propagation Delay: Initial State



### Logic Gate Propagation Delay: Transient



### Logic Gate: Worst Case Scenarios



### Logic Gate Cascade

To avoid large resistance due to many gates in series, logic functions with 4 or more inputs are usually made from cascading two or more 2-4 input blocks.

